

## PERFORMANCE OF DEFECTED GROUND STRUCTURE BASED LPF

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***Abstract-** In this paper we have designed a LPF that is using DGS. In this project a compact microstrip low pass filter is designed using a defected ground structure (DGS) with compensated microstrip. The equivalent circuit for the DGS and its corresponding L-C parameters are extracted by using its S parameters response (EM simulation) and a simple circuit analysis method. The low pass filter is realized and optimized using cascaded DGS to provide a portable size, excellent sharpness in transition with low insertion loss in pass band and wide rejection in the stopband. The proposed periodic defected ground structure (DGS) provides the excellent cutoff and stopband characteristics. In order to show the improved the effective inductance, three DGS circuits were fabricated with identical periodic and different dimensions. Observed results show good agreement with the theoretical results. The results are validated by using CST.*

*Keywords:* LPF, DGS, microstrip, EM simulation.

### **I. Introduction:**

The low pass filter is designed using high and low impedance transmission line sections. The low pass filter prototype element values are calculated for chebyshev response. These lumped element values are translated into distributed element values using standard formulas. The filter is designed in the microstrip configuration, but with air cavities under the inductive lines. The purpose of introducing cavities under the inductive line is to reduce the effective dielectric constant, such that the line widths are convenient to fabricate. Radio frequency (RF) and microwave wireless applications demand compact planar lowpass filters (LPFs), for suppression of noise and interference. Based on the idea of photonic

band-gap structure, defected ground structure was firstly proposed by J.I. Park et al. in 1999[10], which is realized by etching defected patterns on the metallic ground plane under the microstrip line. It has found its applications in planar circuits such as filters [10-12], amplifiers [13] and power dividers [14]. It represents slow-wave and band-stop characteristics by changing the equivalent inductance and the equivalent capacitance of the transmission line. DGS components are the dominant technology which can provide size reduction and has capability of harmonics and spurious suppression. The DGS can be applied to various kinds of components such as lowpass filters (LPFs) and bandpass filters (BPFs) as well as RF phase shifters.

The classic microwave lowpass filter (LPF) is implemented either by all short stubs or by series connected high-low (Hi-Lo) stepped-impedance microstrip line sections. However, these designs suffer from some disadvantages such as the fabrication difficulties associated with the high impedance lines and the appearance of spurious bands. In order to overcome these disadvantages, a method has been proposed in [8,9], which uses both DGS resonators and a compensated microstrip line to design the desired LPF. A method to design lowpass filters (LPF) using defected ground structure (DGS) and compensated microstrip line is presented.

Using the extracted equivalent elements of DGS and capacitive microstrip line, an LPF having no open stub, high impedance line, or cross-junction element, is designed. Only three DGS patterns and one broad microstrip line comprise the LPF. Simple structure, small size (half of a conventional LPF), less discontinuities, and high power handling capability are obtained through the proposed LPF.

### **I.A. Filter design by insertion loss method:**

A filter response is defined by its insertion loss or power loss ratio as:-

$$P_{LR} = \frac{SourcePower}{LoadPower} = \frac{P_{IN}}{P_{OUT}} = \frac{1}{1-|\Gamma(\omega)|^2} \quad (1)$$

As we know that  $|\Gamma(\omega)|^2$  is an even function of  $\omega$ ; therefore it can be expressed as a polynomial in  $\omega$ . Thus we can write

$$|\Gamma(\omega)|^2 = M(\omega^2)/(M(\omega^2)+N(\omega^2)) \quad (2)$$

Where M and N are real polynomials in  $\omega^2$ . Substituting this form in above equation we have:

$$P_{LR} = 1 + (M(\omega^2)/N(\omega^2)) \quad (3)$$

Thus for a filter to be physically realizable its power loss ratio must be of the form as given in above equation. Notice that specifying the power loss ratio simultaneously constrains the reflection coefficient,  $\Gamma(\omega)$ .

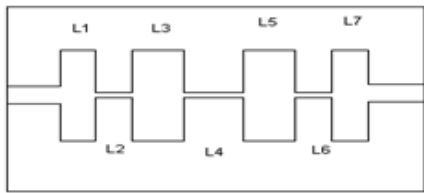


Fig.1:Low Pass Filter Configuration

## II. Analysis of the proposed DGS cell:

Fig.2 shows the proposed DGS cell where transmission line is printed on the GML1000 substrate with a relative permittivity=1 and thickness of  $h=0.762$ mm. The width of the 50Ω transmission line is 0.5mm, and A,B and C are given be 1,0.2 and 3.405 mm, respectively. The novel DGS can equivalent to a simple parallel resonance circuit shown in Fig.2(a), where the equivalent capacitance  $C_p$  and equivalent inductance  $L_p$  can be obtained follows:

$$L_p = 250/C_p(\pi f_0)^2 \text{ nH} \quad (4)$$

$$C_p = 5f_c/\pi(f_0^2 - f_c^2) \text{ pF} \quad (5)$$

Where

$L_p$  = Equivalent Inductance

$C_p$  = Equivalent Capacitance

$F_c$  = Cutoff Frequency

$F_0$  = Center Frequency

For a line with air above the substrate and the effective dielectric constant has values in the range of  $1 < \epsilon_{eff} < \epsilon_r$ . For most applications where the dielectric constant of the substrate is much greater than unity  $\epsilon_r \gg 1$ , the value of  $\epsilon_{eff}$  will be closer to the value of the actual dielectric constant  $\epsilon_r$ , the effective dielectric constant is also a function of frequency.

The initial values (at low frequencies) of the effective dielectric constant are referred to as the *static values*, and they are given by

$$\epsilon_{eff} = \frac{\epsilon_r + 1}{2} + \frac{\epsilon_r - 1}{2} \left[ 1 + 12 \frac{h}{W} \right]^{-1/2} \quad (6)$$

For given dimension of microstrip line, the characteristic is given as :-

$$Z_o = 60 / \sqrt{\epsilon_{eff}} \ln[(8h/W) + (W/4h)] \quad (7)$$

for  $W/h \leq 1$

$$Z_o = 120 / \{ \sqrt{\epsilon_{eff}} [W/h + 1.393 + .667 \ln(W/h + 1.444)] \} \quad (8)$$

for  $W/h > 1$

Size of each DGS is :

$$A=1\text{mm}; \quad B=0.2\text{mm} \quad C=3.405\text{mm}$$

Spacing between each DGS=4.8mm

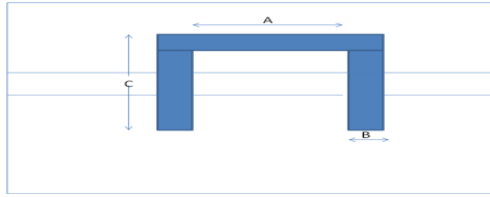


Fig.2:Layout of DGS cell

**III.Simulation Result:**

Fig.: shows the simulated result of the proposed work. The result is realized as given in the table:

Characteristics	Return1	Return2
Frequency	6.292GHz	6.282GHz
Attenuation	65.402dB	62.423dB

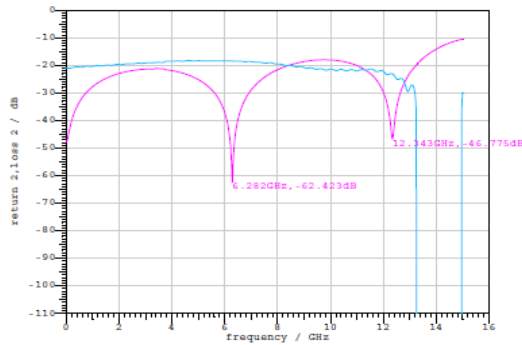


Fig.3:Return2,loss2(dB) vs Frequency(GHz)

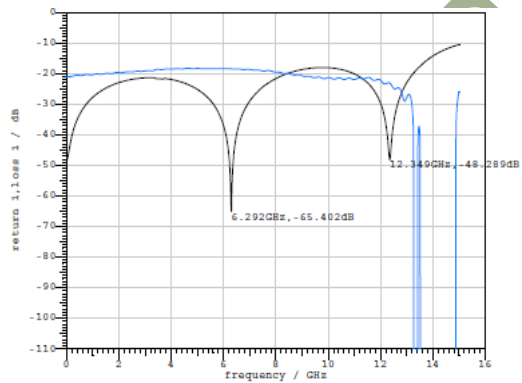


Fig.4:Return1,loss1(dB) vs Frequency(GHz)

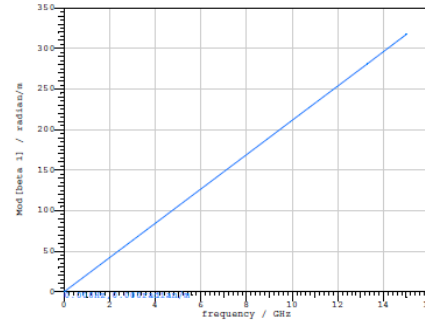


Fig.5:Mod[beta1](radian/m) vs Frequency(GHz)

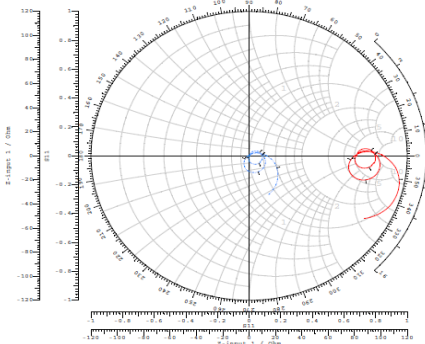


Fig.6: Smith Chart

Z-input1 ——— S<sub>11</sub> -----

(Z-input1) = at 1.637GHz (90.389+5.672i)ohm  
 (1+ S<sub>11</sub>)/(1- S<sub>11</sub>) = at 1.199GHz(1.066+0.072i)

**XI. CONCLUSION**

A new concept of a compact LPF using three U-DGSs has been proposed. This lowpass filter is not only of compact size, but also offers control of the cutoff frequency and transmission zero. To verify the performance, the fabrication, simulation and measurement of the filter was done. The measurements show a good consistency with the simulations. Therefore, it is expected that the proposed structures with its compact size, simple circuitry and large stopband characteristics will be used for applications in various integrated microwave circuits as well as other types of filters. The microstrip lowpass filters show advantages of high performance, low cost, and easy fabrication. Measured results are in good agreement with simulated results. A new LPF using only three DGS patterns and compensated

microstrip line is proposed. No open stubs, high impedances lines, and cross-junction are required. This makes the proposed LPF suitable for high power application.

The advantages of this LPF are:

1. Suppressing higher harmonic.
2. Achieving broader stopband responses.
3. Improving the stop and pass band characteristics.
4. Better frequency responses in the passband.
5. Fewer losses in passband.
6. A very sharp transition response.

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Meenu Bhati is pursued Diploma in (EC) Electronics & Communication from Govt. Polytechnic College, CHURU. **B.Tech.** in Electronics and communication Engineering. From Govt. ECB Bikaner under Rajasthan

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2003 shifted to Jaipur and joined the profession of teaching and from last eight years working as professor and head of electronics department in various engineering collages. At present he is working as head and Professor in the department of Electronics and communication Engineering at JNU, Jaipur.



Professor **Rajeshwar Lal Dua** a Fellow Life Member of IETE and also a Life member of: I.V.S & I.P.A former "ScientistF"(Deputy Director) of the Central Electronics

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He was awarded a degree of M.Sc (Physics) and M.Sc Tech (Electronics) from BITS Pilani. He started his professional carrier in 1966 at Central Electronics Engineering Research Institute (CEERI), Pilani. During this period, indigenous know how was developed for several types of fixed frequency and tunable magnetrons of conventional and coaxial type. He headed the team for the production of specific Magnetrons for defense and transferred the know how to industries for further production. He also has several publications and a patent to his credit.

In 1979 he visited department of Electrical and Electronics Engineering at the University Of Sheffield (UK) in the capacity of independent research worker, and Engineering Department of Cambridge University Cambridge (UK) as a visiting scientist. After retirement as scientist in